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Meeting review ST-CNES STRH12P10 dynamic test

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The T_{rr} and switching times provided at the qualification time (~15 years ago) were defined without sufficient margin vs. the limits. As consequence ESCC and data-sheet are not aligned with the real characteristics.

REVERSE RECOVERY TIME (T_{rr})

The actual ESCC detailed spec and ST data-sheet are:

- $ISD = 12A$, $di/dt = 40 A/\mu s$, $VDD = 60V$, $T_j = 25^\circ C$ max 258 ns.
- $ISD = 12 A$, $di/dt = 40 A/\mu s$, $VDD = 60 V$, $T_j = 150^\circ C$ max 335 ns

Since long time no parts have been tested and, in a recent characterization, values above the max limit have been found.

Also the condition of $ISD = 12A$ shows some abnormal instability due to the high value of the reverse recovery current (IRRM) of about 20A required to achieve $ISD = 12A$.

To avoid mismatch and solve the issue, T_{rr} has been characterized at different conditions and the best trade-off have been found as follows. As consequence ST is proposing to modify the test according to.

- $ISD = 6A$, $di/dt = 50A/\mu s$, $VDD = 50 V$, $T_j = 25^\circ C$ max 310 ns.
- $ISD = 6A$, $di/dt = 50 A/\mu s$, $VDD = 50 V$, $T_j = 150^\circ C$ max 400 ns

> At $ISD = 6A$ the correspondent IRRM is about 11A which is a more stable condition for the device.

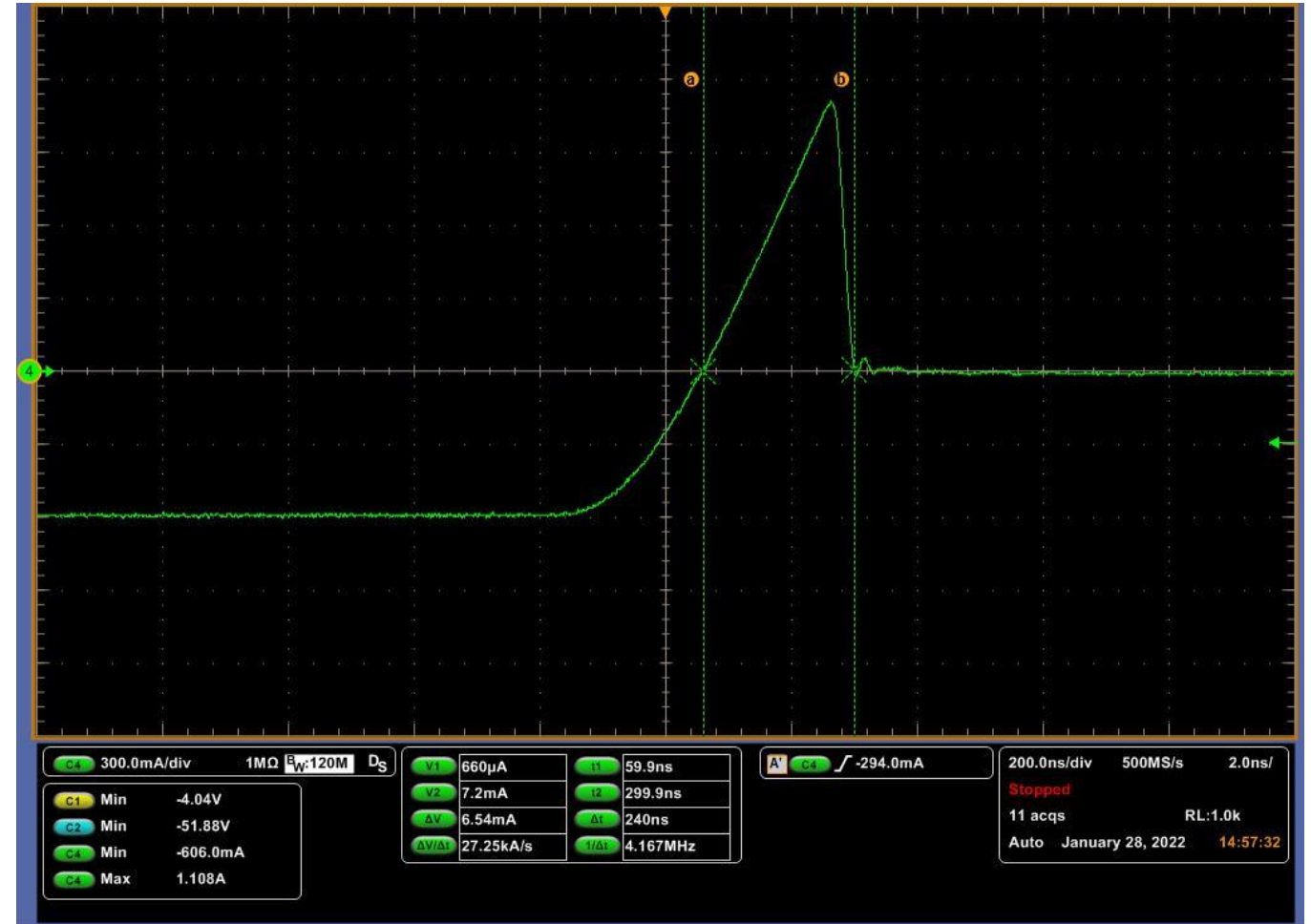
Reverse Recovery Time waveform

Test conditions

$V_{dd} = -50V$
 $I_d = -6A$
 $di/dt = 50A/\mu s$
 $T_j = 25^\circ C$

Measurements

I_{rm} (A)	T_{Irm} (ns)	T_{rr} (ns)	Q_{rr} (nC)
11.1	206	242	1345



- I_d (ch4) = 3A/div
- $t = 200ns/div$

STRH12P10 switching times

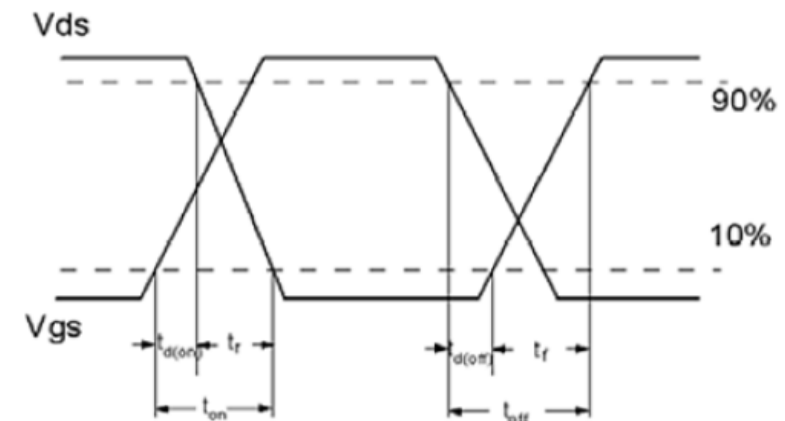
- During the characterization also Tdon and Tdoff has been noted with values too close to the max limit.
- To reduce marginality, new limits are proposed with an increase of 20%.

Test	value	Actual max	New max
t_{don} (ns)	12.5	13	15.6
t_{doff} (ns)	41.0	42	50.4

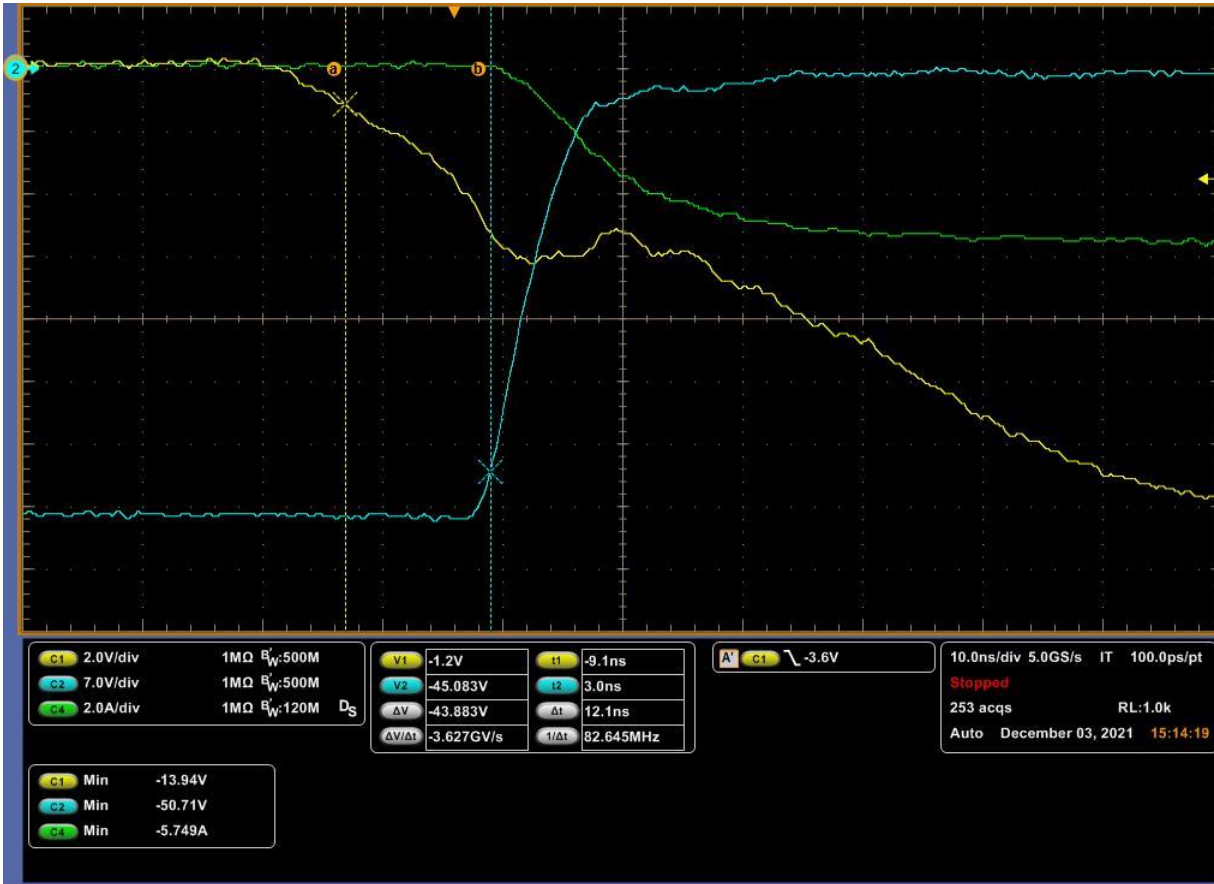
Conditions remain unchanged

$V_{dd} = -50V$
 $I_d = -6A$
 $V_{gs} = -12V$
 $R_g = 4.7\Omega$
 $T_c = 25^\circ C$

Test method and measurement points

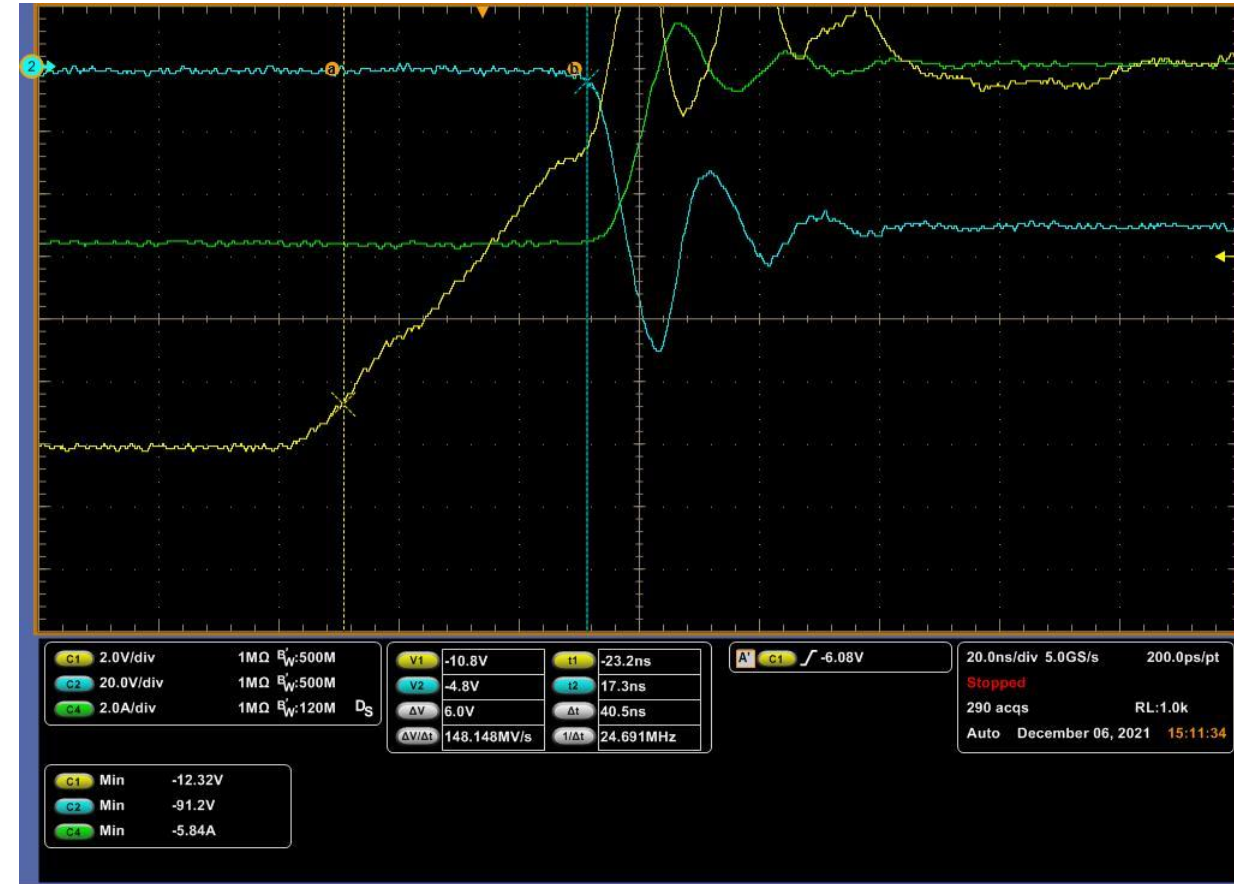


STRH12P10 switching times waveforms



t_{don}

- Id (ch4) = 2A/div
- Vds (ch2) = 7V/div
- Vgate (ch1) = 2V/div
- t = 10ns/div



t_{doff}

- Id (ch4) = 2A/div
- Vds (ch2) = 20V/div
- Vgate= ch1=2V/div
- t=20ns/div

- Recent dynamic characterization has been performed on a significant number of devices.
- It has been detected poor marginality and unstable measurements vs. the actual conditions and limits.
- No diffusion process has been changed since the qualification.
- New limits and conditions have been defined to reflect the product's characteristics.
- From application and reliability perspective there is no impact in terms of performance or stability.
- Formal notification will be provided to Agencies (DCR) and customers.

Thank you

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